Silicon Power Transistors

The MJL21193 and MJL21194 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

- Total Harmonic Distortion Characterized
- High DC Current Gain hFE = 25 Min @ IC = 8 Adc WWW.DZSC.COM
- Excellent Gain Linearity
- High SOA: 2.25 A, 80 V, 1 Second

PNP MJL21193* **MJL2119**

*Motorola Preferred Device

16 AMPERE **COMPLEMENTARY** SILICON POWER **TRANSISTORS 250 VOLTS 200 WATTS**



CASE 340G-02 TO-3PBL

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|--------------|---------------|
| Collector–Emitter Voltage | VCEO | 250 | Vdc |
| Collector-Base Voltage | VCBO | 400 | Vdc |
| Emitter–Base Voltage | VEBO | 5 | Vdc |
| Collector–Emitter Voltage – 1.5 V | VCEX | 400 | Vdc |
| Collector Current — Continuous Peak (1) | lC | 16 30 | Adc |
| Base Current - Continuous | lВ | 5 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate Above 25°C | PD | 200 1.43 | Watts W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | - 65 to +150 | °C |

THERMAL CHARACTERISTICS

lf.dzsc.com

| Characteristic | Symbol | Max | Unit |
|--------------------------------------|-----------------|-----|------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 0.7 | °C/W |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typical | Max | Unit | |
|--|-----------|-----|---------|-----|------|--|
| OFF CHARACTERISTICS | | | | | | |
| Collector–Emitter Sustaining Voltage (I _C = 100 mAdc, I _B = 0) | VCEO(sus) | 250 | _ | _ | Vdc | |
| Collector Cutoff Current (V _{CE} = 200 Vdc, I _B = 0) | ICEO | _ | _ | 100 | μAdc | |

(1) Pulse Test: Pulse Width = $5.0 \,\mu s$, Duty Cycle $\leq 10\%$.

(continued)



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$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_C = 25^{\circ}\text{C unless otherwise noted})$

| Characteristic | | Symbol | Min | Typical | Max | Unit |
|---|-----------------------------|----------------------|-------------|---------|----------|------|
| OFF CHARACTERISTICS | | • | | | | |
| Emitter Cutoff Current (VCE = 5 Vdc, IC = 0) | | I _{EBO} | _ | _ | 100 | μAdc |
| Collector Cutoff Current (VCE = 250 Vdc, VBE(off) = 1.5 Vdc) | | ICEX | _ | _ | 100 | μAdc |
| SECOND BREAKDOWN | | • | | • | | |
| Second Breakdown Collector Current with Base Form (VCE = 50 Vdc, t = 1 s (non-repetitive) (VCE = 80 Vdc, t = 1 s (non-repetitive) | ward Biased | ^I S/b | 4.0 2.25 | _ | | Adc |
| ON CHARACTERISTICS | | | | • | | |
| DC Current Gain (I _C = 8 Adc, V _{CE} = 5 Vdc) (I _C = 16 Adc, I _B = 5 Adc) | | hFE | 25 8 | | 75 — | |
| Base–Emitter On Voltage (I _C = 8 Adc, V _{CE} = 5 Vdc) | | V _{BE} (on) | _ | _ | 2.2 | Vdc |
| Collector–Emitter Saturation Voltage (I _C = 8 Adc, I _B = 0.8 Adc) (I _C = 16 Adc, I _B = 3.2 Adc) | | VCE(sat) | _ | _ | 1.4 4 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | • | | • |
| Total Harmonic Distortion at the Output V _{RMS} = 28.3 V, f = 1 kHz, P _{LOAD} = 100 W _{RMS} | hFE | T _{HD} | | | | % |
| (Matched pair h _{FE} = 50 @ 5 A/5 V) | unmatched hFE matched | | _ | 0.8 | _ _ | |
| Current Gain Bandwidth Product (I _C = 1 Adc, V _{CE} = 10 Vdc, f _{test} = 1 MHz) | | fΤ | 4 | _ | _ | MHz |
| Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz) | | C _{ob} | _ | _ | 500 | pF |

⁽¹⁾ Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2%

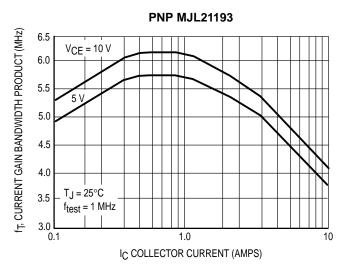


Figure 1. Typical Current Gain Bandwidth Product

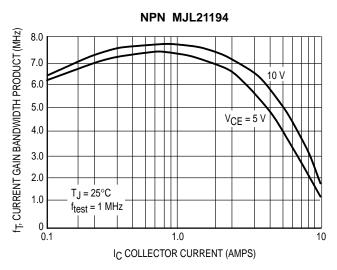


Figure 2. Typical Current Gain Bandwidth Product

TYPICAL CHARACTERISTICS

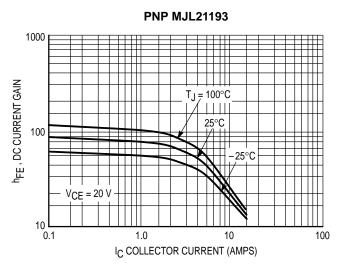


Figure 3. DC Current Gain, V_{CE} = 20 V

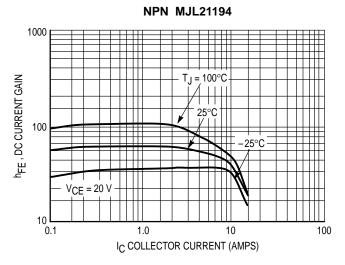


Figure 4. DC Current Gain, V_{CE} = 20 V

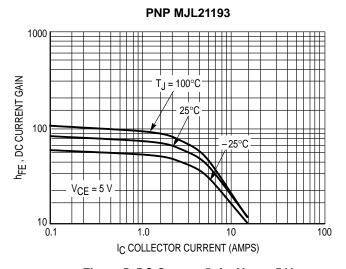


Figure 5. DC Current Gain, V_{CE} = 5 V

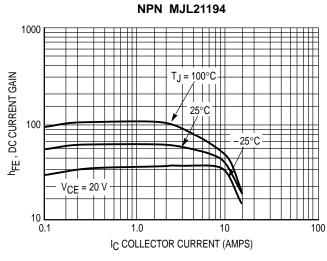


Figure 6. DC Current Gain, V_{CE} = 5 V

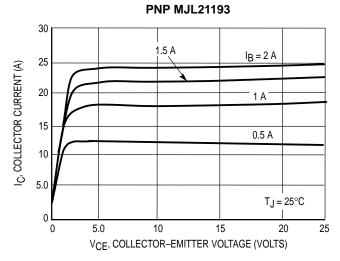


Figure 7. Typical Output Characteristics

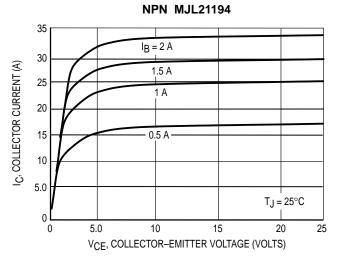


Figure 8. Typical Output Characteristics

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TYPICAL CHARACTERISTICS

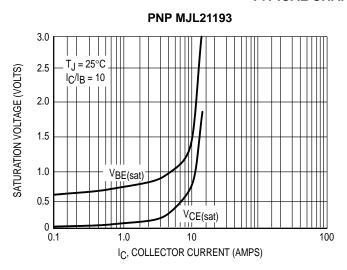


Figure 9. Typical Saturation Voltages

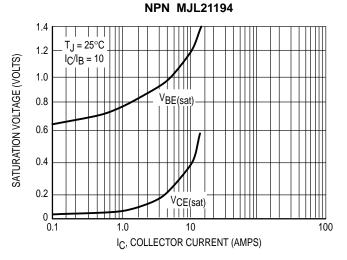


Figure 10. Typical Saturation Voltages

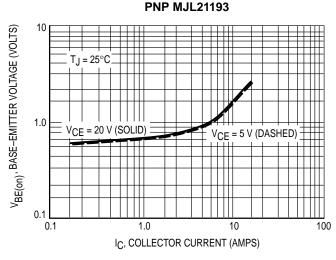


Figure 11. Typical Base-Emitter Voltage

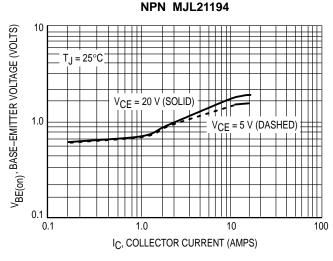


Figure 12. Typical Base-Emitter Voltage

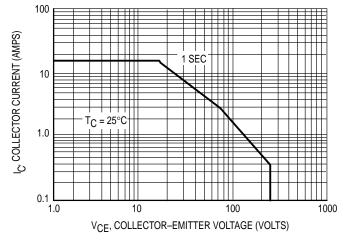
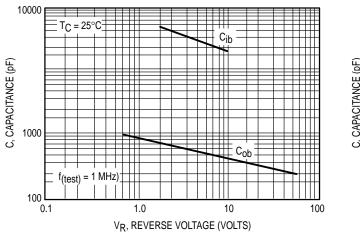


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate IC - VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

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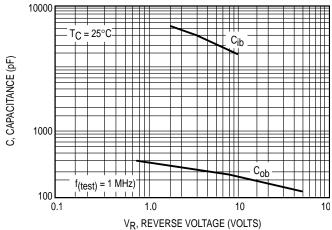


Figure 14. MJL21193 Typical Capacitance

Figure 15. MJL21194 Typical Capacitance

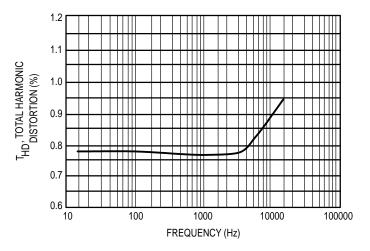


Figure 16. Typical Total Harmonic Distortion

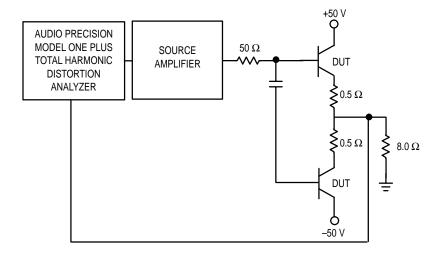
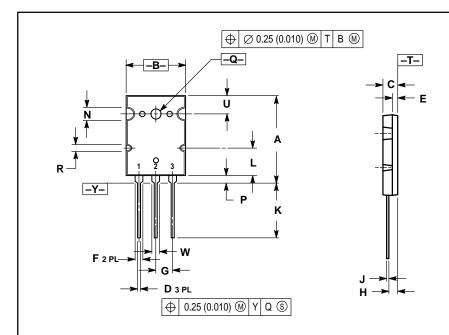


Figure 17. Total Harmonic Distortion Test Circuit

PACKAGE DIMENSIONS



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

| | MILLIN | IETERS | INC | HES | |
|-----|--------|--------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 2.8 | 2.9 | 1.102 | 1.142 | |
| В | 19.3 | 20.3 | 0.760 | 0.800 | |
| С | 4.7 | 5.3 | 0.185 | 0.209 | |
| D | 0.93 | 1.48 | 0.037 | 0.058 | |
| Е | 1.9 | 2.1 | 0.075 | 0.083 | |
| F | 2.2 | 2.4 | 0.087 | 0.102 | |
| G | 5.45 | BSC | 0.215 BSC | | |
| Н | 2.6 | 3.0 | 0.102 | 0.118 | |
| J | 0.43 | 0.78 | 0.017 | 0.031 | |
| K | 17.6 | 18.8 | 0.693 | 0.740 | |
| L | 11.0 | 11.4 | 0.433 | 0.449 | |
| N | 3.95 | 4.75 | 0.156 | 0.187 | |
| P | 2.2 | 2.6 | 0.087 | 0.102 | |
| Q | 3.1 | 3.5 | 0.122 | 0.137 | |
| R | 2.15 | 2.35 | 0.085 | 0.093 | |
| U | 6.1 | 6.5 | 0.240 | 0.256 | |
| W | 2.8 | 3.2 | 0.110 | 0.125 | |

STYLE 2: PIN 1. BASE

COLLECTOR EMITTER

CASE 340G-02 TO-3PBL **ISSUE E**

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